

# Davit A Ghazaryan

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6520997/publications.pdf>

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13  
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1125743

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docs citations

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1824  
citing authors

#	ARTICLE	IF	CITATIONS
1	Twisted monolayer and bilayer graphene for vertical tunneling transistors. Applied Physics Letters, 2021, 118, .	3.3	7
2	On the Role of Structural Imperfections of Graphene in Resonant Tunneling through Localized States in the h-BN Barrier of van-der-Waals Heterostructures. Semiconductors, 2020, 54, 291-296.	0.5	0
3	Field-induced insulating states in a graphene superlattice. Physical Review B, 2019, 99, .	3.2	2
4	High-temperature electronic devices enabled by hBN-encapsulated graphene. Applied Physics Letters, 2019, 114, .	3.3	32
5	Engineering Graphene Flakes for Wearable Textile Sensors <i>via</i> Highly Scalable and Ultrafast Yarn Dyeing Technique. ACS Nano, 2019, 13, 3847-3857.	14.6	179
6	Planar and van der Waals heterostructures for vertical tunnelling single electron transistors. Nature Communications, 2019, 10, 230.	12.8	43
7	Unusual Suppression of the Superconducting Energy Gap and Critical Temperature in Atomically Thin NbSe <sub>2</sub> . Nano Letters, 2018, 18, 2623-2629.	9.1	70
8	Graphene hot-electron light bulb: incandescence from hBN-encapsulated graphene in air. 2D Materials, 2018, 5, 011006.	4.4	43
9	Tunnel spectroscopy of localised electronic states in hexagonal boron nitride. Communications Physics, 2018, 1, .	5.3	33
10	Magnon-assisted tunnelling in van der Waals heterostructures based on CrBr <sub>3</sub> . Nature Electronics, 2018, 1, 344-349.	26.0	239
11	Stacking transition in bilayer graphene caused by thermally activated rotation. 2D Materials, 2017, 4, 011013.	4.4	20
12	Tuning the valley and chiral quantum state of Dirac electrons in van der Waals heterostructures. Science, 2016, 353, 575-579.	12.6	88
13	Phonon-Assisted Resonant Tunneling of Electrons in Graphene-Boron Nitride Transistors. Physical Review Letters, 2016, 116, 186603.	7.8	78